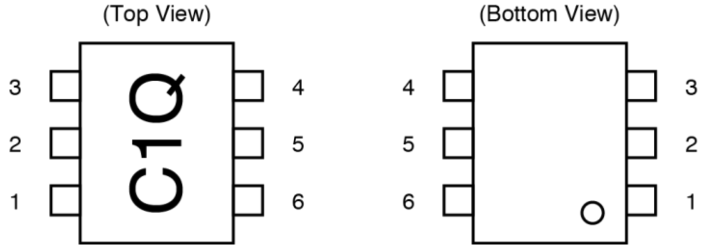
PIN CONNECTION



Marking is an example of μPC2745TB

Pin No.	Pin Name
1	INPUT
2	GND
3	GND
4	OUTPUT
5	GND
6	V_{CC}

PRODUCT LINE-UP (T_A = +25°C, V_{CC} = 3.0 V, Z_S = Z_L = 50 Ω)

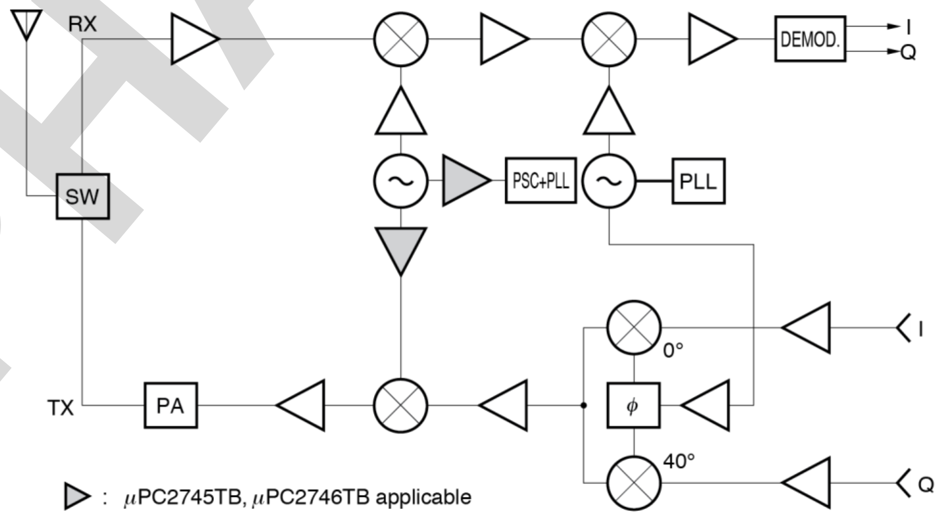
Part No.	f_u (GHz)	$P_{O(sat)}$ (dBm)	G_P (dB)	NF (dB)	I_{CC} (mA)	Package	Making
μPC2745T	2.7	−1.0	12	6.0	7.5	6-pin minimold	C1Q
μPC2745TB						6-pin super minimold	
μPC2746T	1.5	0	19	4.0	7.5	6-pin minimold	C1R
μPC2746TB						6-pin super minimold	
μPC2747T	1.8	−7.0	12	3.3	5.0	6-pin minimold	C1S
μPC2747TB						6-pin super minimold	
μPC2748T	0.2 to 1.5	−3.5	19	2.8	6.0	6-pin minimold	C1T
μPC2748TB						6-pin super minimold	
μPC2749T	2.9	−6.0	16	4.0	6.0	6-pin minimold	C1U
μPC2749TB						6-pin super minimold	

Remark Typical performance. Please refer to **ELECTRICAL CHARACTERISTICS** in detail.

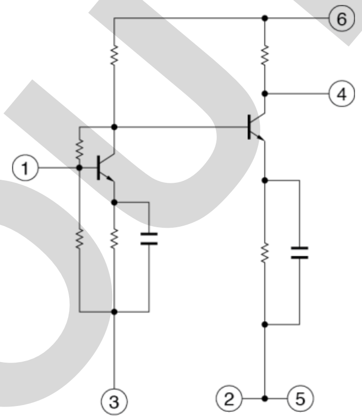
Caution The package size distinguish between minimold and super minimold.

SYSTEM APPLICATION EXAMPLE

DIGITAL CELLULAR SYSTEM BLOCK DIAGRAM



PIN EXPLANATION

Pin No.	Pin Name	Applied Voltage (V)	Pin Voltage (V)Note	Function and Applications	Internal Equivalent Circuit
1	INPUT	—	0.87 0.82	Signal input pin. A internal matching circuit, configured with resistors, enables 50 Ω connection over a wide band. this pin must be coupled to signal source with capacitor for DC cut.	
2 3 5	GND	0	—	Ground pin. This pin should be connected to system ground with minimum inductance. Ground pattern on the board should be formed as wide as possible. All the ground pins must be connected together with wide ground pattern to decrease impedance difference.	
4	OUTPUT	—	1.95 2.54	Signal output pin. A internal matching circuit, configured with resistors, enables 50 Ω connection over a wide band. This pin must be coupled to next stage with capacitor for DC cut.	
6	V_{CC}	2.7 to 3.3	—	Power supply pin. This pin should be externally equipped with bypass capacity to minimize ground impedance.	

Note Pin voltage is measured at V_{CC} = 3.0 V. Above: μPC2745TB, Below: μPC2746TB

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Conditions	Ratings	Unit
Supply Voltage	V_{CC}	T_A = +25°C	4.0	V
Circuit Current	I_{CC}	T_A = +25°C	16	mA
Power Dissipation	P_D	T_A = +85°C **Note**	270	mW
Operating Ambient Temperature	T_A		–40 to +85	°C
Storage Temperature	T_{stg}		–55 to +150	°C
Input Power	P_{in}	T_A = +25°C	0	dBm

Note Mounted on double-sided copper-clad 50 × 50 × 1.6 mm epoxy glass PWB

RECOMMENDED OPERATING RANGE

Parameter	Symbol	MIN.	TYP.	MAX.	Unit
Supply Voltage	V_{CC}	2.7	3.0	3.3	V

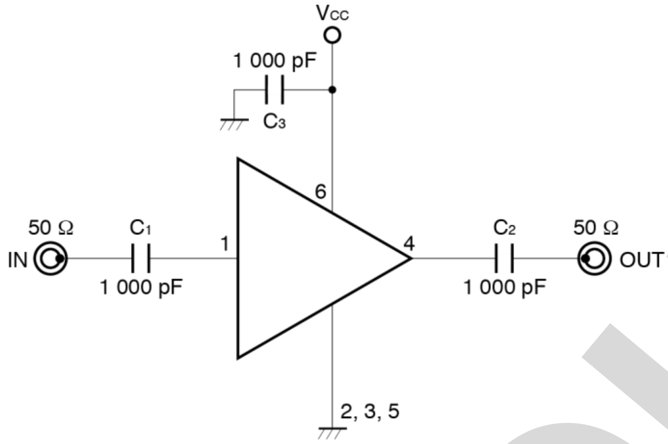
ELECTRICAL CHARACTERISTICS
(T_A = +25°C, V_{CC} = 3.0 V, Z_S = Z_L = 50 Ω, unless otherwise specified)

Parameter	Symbol	Test Conditions	μPC2745TB			μPC2746TB			Unit
			MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
Circuit Current	I_{CC}	No signal	5.0	7.5	10.0	5.0	7.5	10.0	mA
Power Gain	G_P	f = 500 MHz	9	12	14	16	19	21	dB
Noise Figure	NF	f = 500 MHz	—	6.0	7.5	—	4.0	5.5	dB
Upper Limit Operating Frequency	f_u	3 dB down below from gain at f = 0.1 GHz	2.3	2.7	—	1.1	1.5	—	GHz
Isolation	ISL	f = 500 MHz	33	38	—	40	45	—	dB
Input Return Loss	RL_{in}	f = 500 MHz	8	11	—	10	13	—	dB
Output Return Loss	RL_{out}	f = 500 MHz	2.5	5.5	—	5.5	8.5	—	dB
Saturated Output Power	$P_{O(sat)}$	f = 500 MHz, P_{in} = –6 dBm	–4.0	–1.0	—	–3.0	0	—	dBm

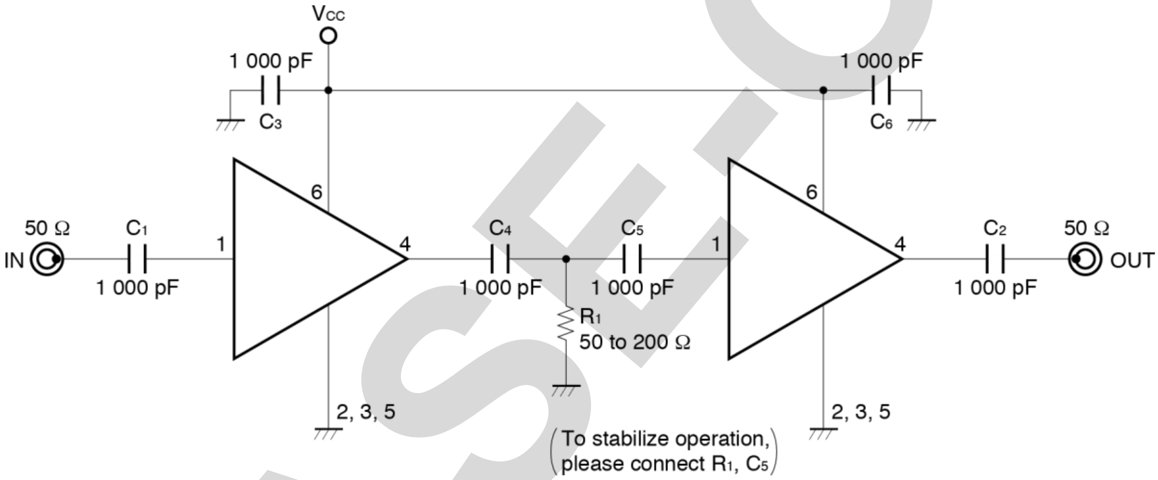
STANDARD CHARACTERISTICS FOR REFERENCE (T_A = +25°C, V_{CC} = 3.0 V, Z_S = Z_L = 50 Ω)

Parameter	Symbol	Test Conditions	Reference Value		Unit
			μPC2745TB	μPC2746TB	
Circuit Current	I_{CC}	V_{CC} = 1.8 V, No signal	4.5	4.5	mA
Power Gain	G_P	V_{CC} = 3.0 V, f = 1.0 GHz V_{CC} = 3.0 V, f = 2.0 GHz V_{CC} = 1.8 V, f = 0.5 GHz	12.0 11.0 7.0	18.5 — 14.0	dB
Noise Figure	NF	V_{CC} = 3.0 V, f = 1.0 GHz V_{CC} = 3.0 V, f = 2.0 GHz V_{CC} = 1.8 V, f = 0.5 GHz	5.5 5.7 8.0	4.2 — 5.0	dB
Upper Limit Operating Frequency	f_u	V_{CC} = 1.8 V, 3 dB down below from gain at f = 0.1 GHz	1.8	1.1	GHz
Isolation	ISL	V_{CC} = 3.0 V, f = 1.0 GHz V_{CC} = 3.0 V, f = 2.0 GHz V_{CC} = 1.8 V, f = 0.5 GHz	33 30 35	38 — 37	dB
Input Return Loss	RL_{in}	V_{CC} = 3.0 V, f = 1.0 GHz V_{CC} = 3.0 V, f = 2.0 GHz V_{CC} = 1.8 V, f = 0.5 GHz	13.0 14.0 6.5	10.0 — 10.0	dB
Output Return Loss	RL_{out}	V_{CC} = 3.0 V, f = 1.0 GHz V_{CC} = 3.0 V, f = 2.0 GHz V_{CC} = 1.8 V, f = 0.5 GHz	6.5 8.5 6.0	8.5 — 9.5	dB
Saturated Output Power	$P_{O(sat)}$	V_{CC} = 3.0 V, f = 1.0 GHz, P_{in} = –6 dBm V_{CC} = 3.0 V, f = 2.0 GHz, P_{in} = –6 dBm V_{CC} = 1.8 V, f = 0.5 GHz, P_{in} = –10 dBm	–2.5 –3.5 –11.0	–1.0 — –8.0	dBm
★ 3rd Order Intermodulation Distortion	IM_3	V_{CC} = 3.0 V, P_{out} = –10 dBm, f_1 = 500 MHz, f_2 = 502 MHz V_{CC} = 1.8 V, P_{out} = –20 dBm, f_1 = 500 MHz, f_2 = 502 MHz V_{CC} = 3.0 V, P_{out} = –10 dBm, f_1 = 1 000 MHz, f_2 = 1 002 MHz	–30.0 –31.0 –26.0	–26.0 –37.0 —	dBc

TEST CIRCUIT



EXAMPLE OF APPLICATION CIRCUIT



The application circuits and their parameters are for references only and are not intended for use in actual design-ins.

CAPACITORS FOR THE VCC, INPUT, AND OUTPUT PINS

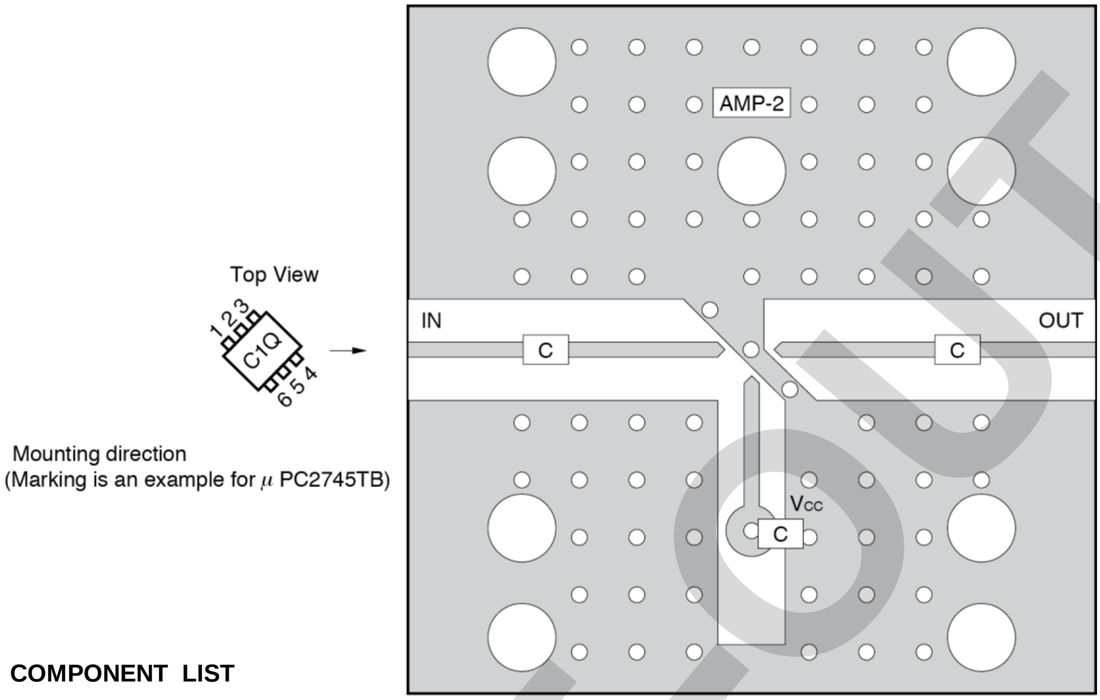
Capacitors of 1 000 pF are recommendable as the bypass capacitor for the VCC pin and the coupling capacitors for the input and output pins.

The bypass capacitor connected to the VCC pin is used to minimize ground impedance of VCC pin. So, stable bias can be supplied against VCC fluctuation.

The coupling capacitors, connected to the input and output pins, are used to cut the DC and minimize RF serial impedance. Their capacitance are therefore selected as lower impedance against a 50 Ω load. The capacitors thus perform as high pass filters, suppressing low frequencies to DC.

To obtain a flat gain from 100 MHz upwards, 1 000 pF capacitors are used in the test circuit. In the case of under 10 MHz operation, increase the value of coupling capacitor such as 10 000 pF. Because the coupling capacitors are determined by equation, $fc = 1/(2\pi RC)$.

ILLUSTRATION OF THE TEST CIRCUIT ASSEMBLED ON EVALUATION BOARD



COMPONENT LIST

	Value
C	1 000 pF

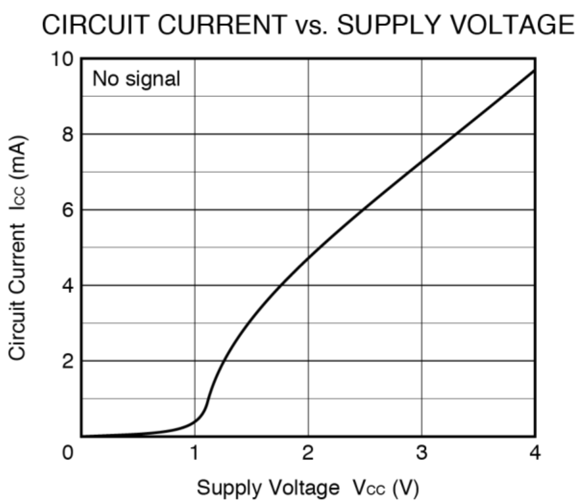
Notes

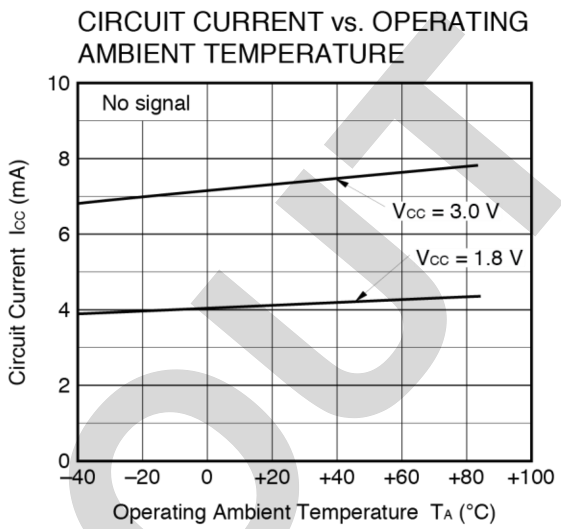
1. 30 × 30 × 0.4 mm double sided copper clad polyimide board.
2. Back side: GND pattern
3. Solder plated on pattern
4. ○ ○ ○ : Through holes

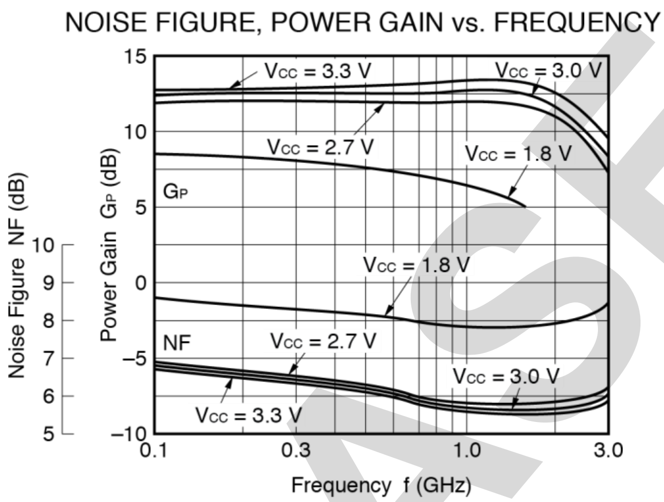
For more information on the use of this IC, refer to the following application note: **USAGE AND APPLICATIONS OF 6-PIN MINI-MOLD, 6-PIN SUPER MINI-MOLD SILICON HIGH-FREQUENCY WIDEBAND AMPLIFIER MMIC (P11976E).**

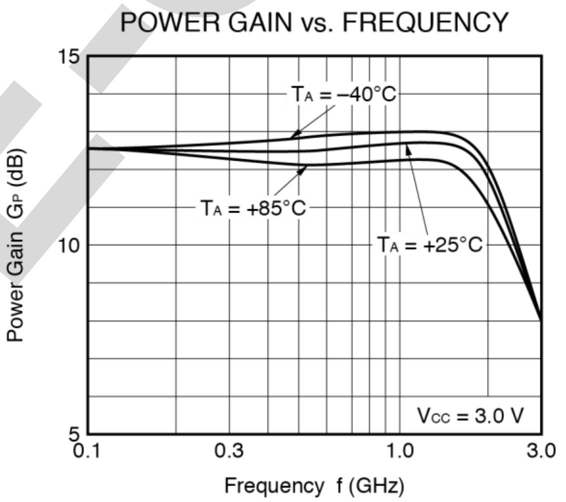
TYPICAL CHARACTERISTICS (TA = +25°C, unless otherwise specified)

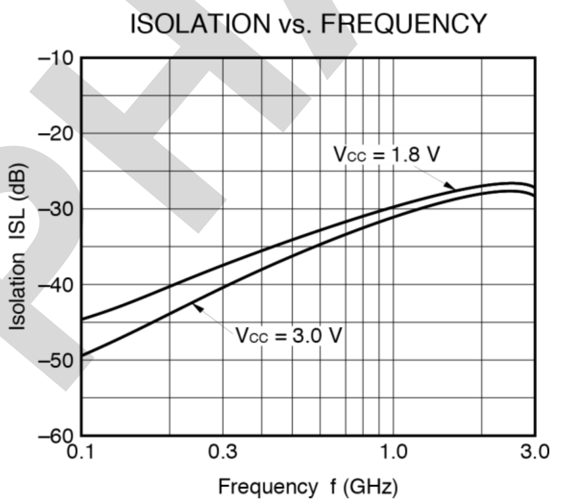
— μPC2745TB —

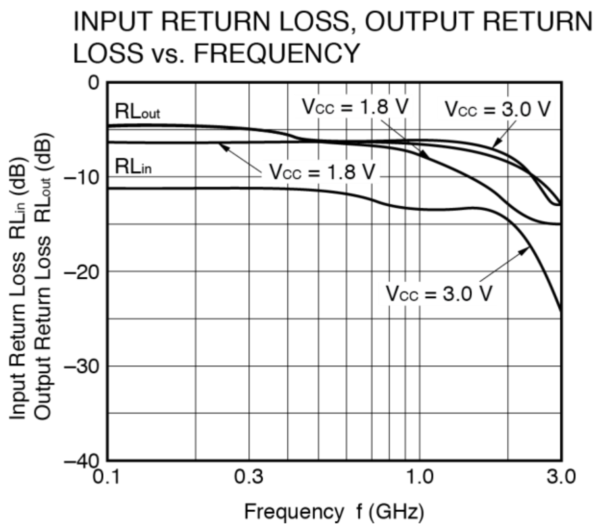








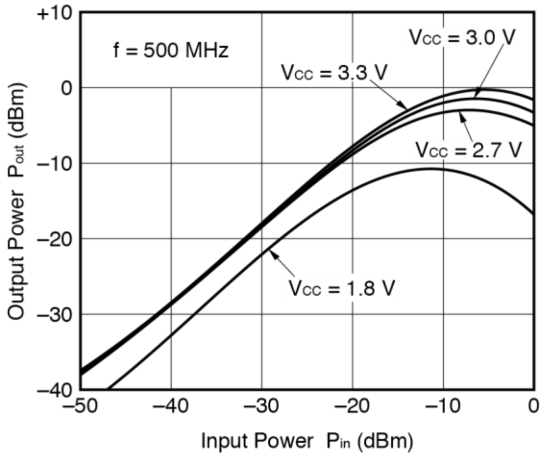




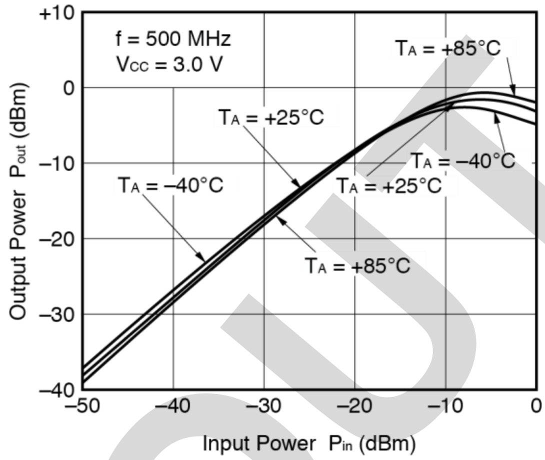
Remark The graphs indicate nominal characteristics.

— μPC2745TB —

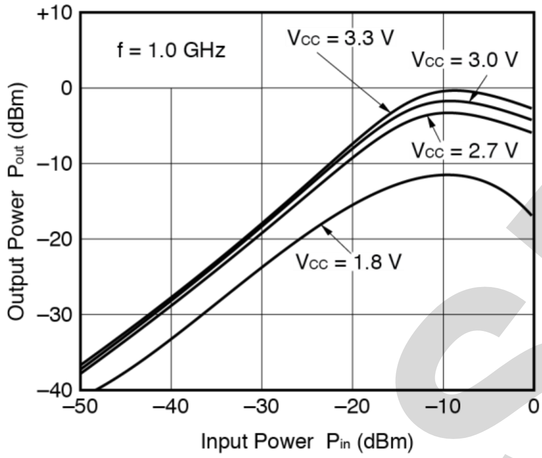
OUTPUT POWER vs. INPUT POWER



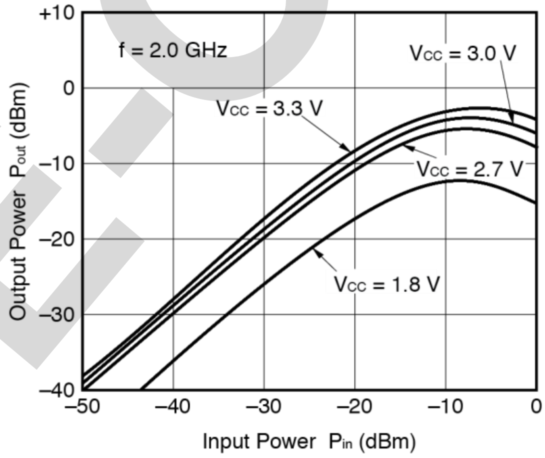
OUTPUT POWER vs. INPUT POWER



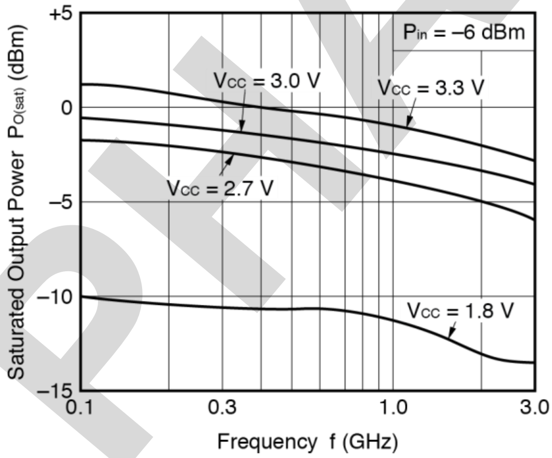
OUTPUT POWER vs. INPUT POWER



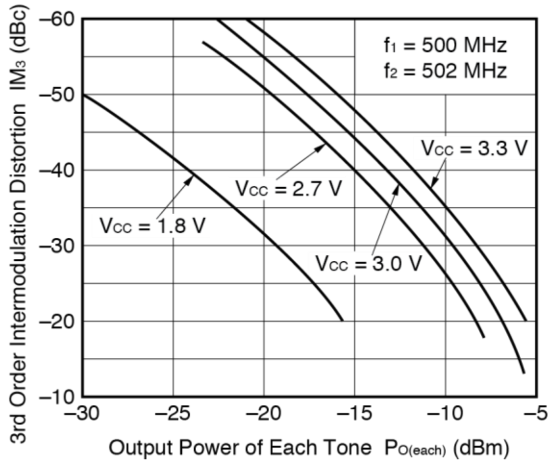
OUTPUT POWER vs. INPUT POWER



SATURATED OUTPUT POWER vs. FREQUENCY



3RD ORDER INTERMODULATION DISTORTION vs. OUTPUT POWER OF EACH TONE

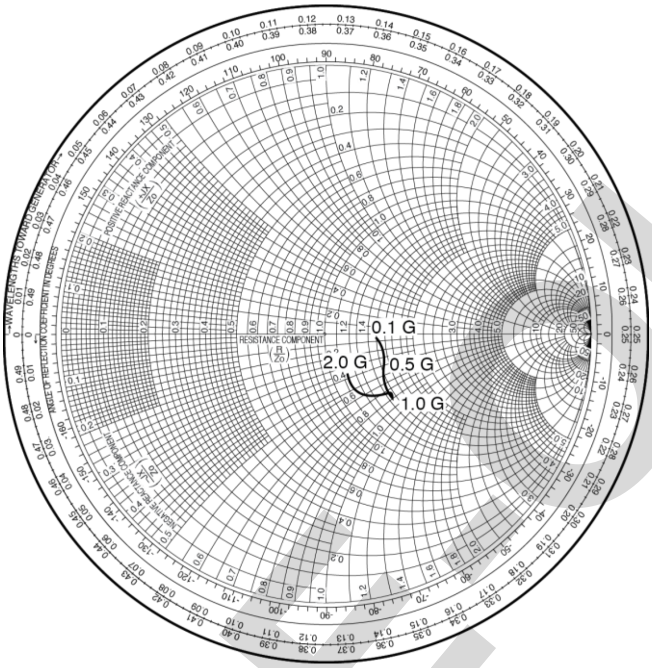


Remark The graphs indicate nominal characteristics.

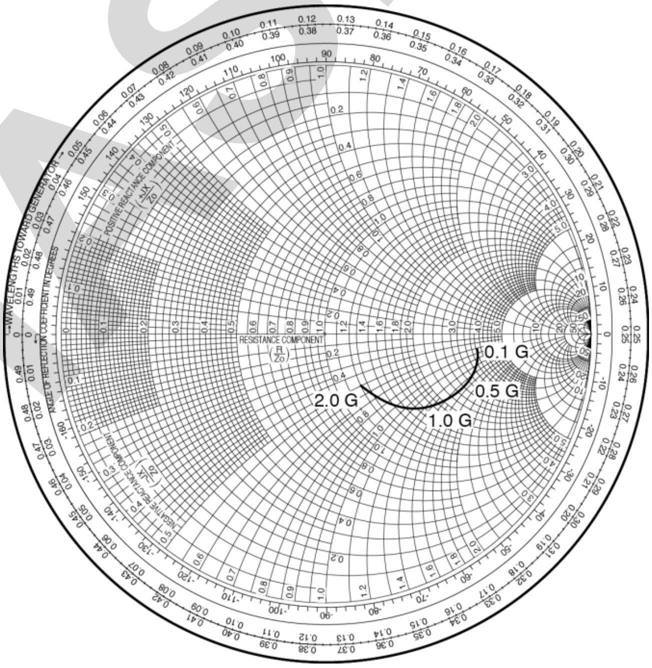
SMITH CHART (T_A = +25°C, V_{CC} = 3.0 V)

— μPC2745TB —

S_{11}-FREQUENCY



S_{22}-FREQUENCY



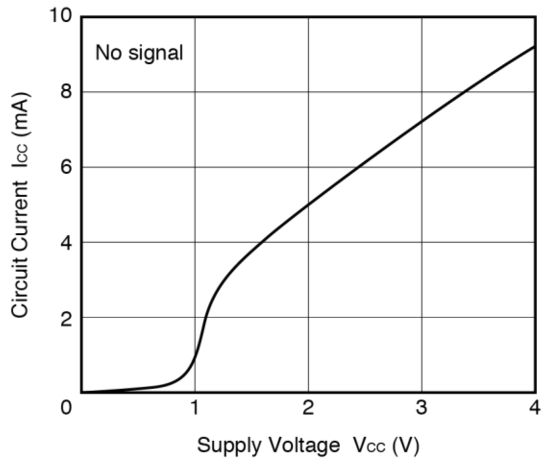
S-PARAMETERS

- S-parameters and noise parameters are provided on our Web site in a format (S2P) that enables the direct import of the parameters to microwave circuit simulators without the need for keyboard inputs.
- Click here to download S-parameters.
- [RF and Microwave] ® [Device Parameters]
- URL http://www.necel.com/microwave/en/

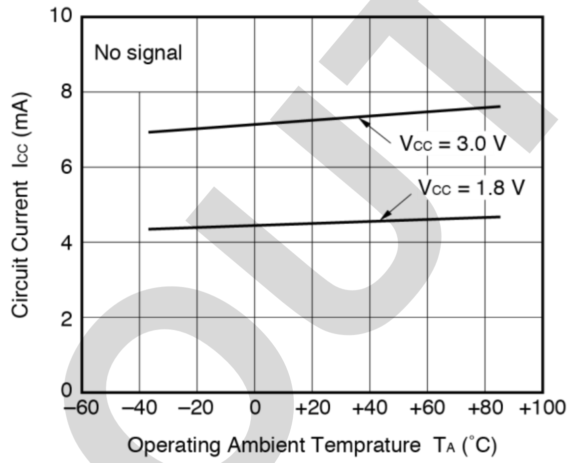
TYPICAL CHARACTERISTICS (T_A = +25°C, unless otherwise specified)

— μPC2746TB —

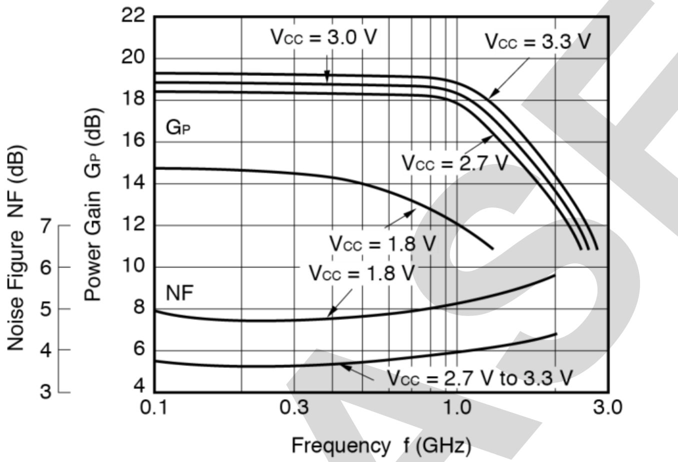
CIRCUIT CURRENT vs. SUPPLY VOLTAGE



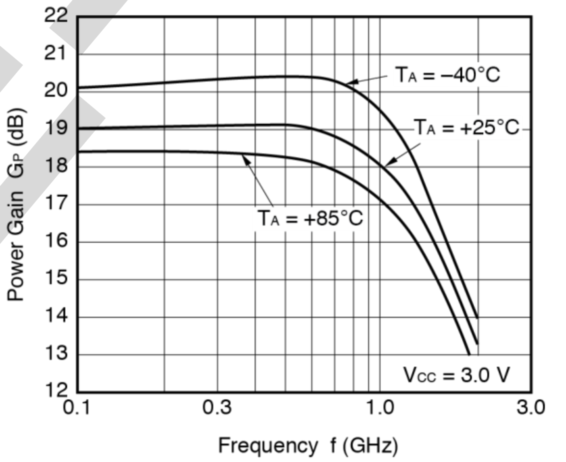
CIRCUIT CURRENT vs.
OPERATING AMBIENT TEMPERATURE



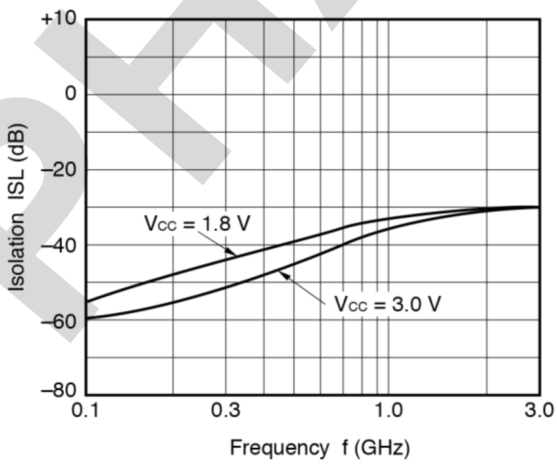
NOISE FIGURE, POWER GAIN vs. FREQUENCY



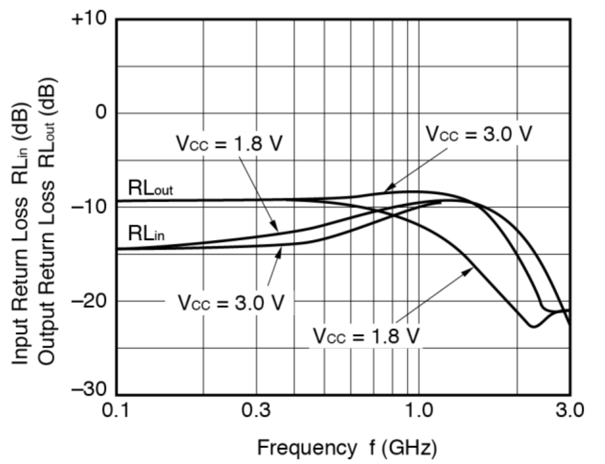
POWER GAIN vs. FREQUENCY



ISOLATION vs. FREQUENCY



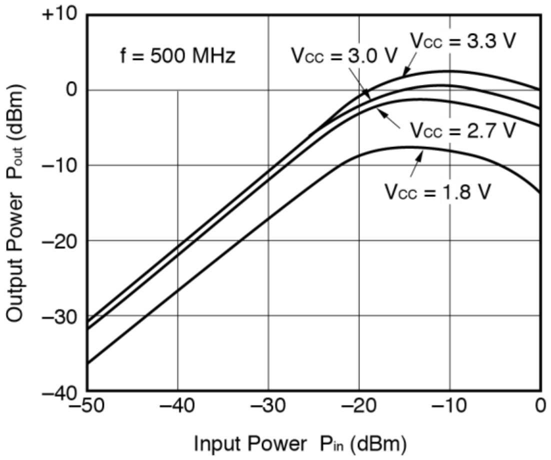
INPUT RETURN LOSS, OUTPUT RETURN
LOSS vs. FREQUENCY



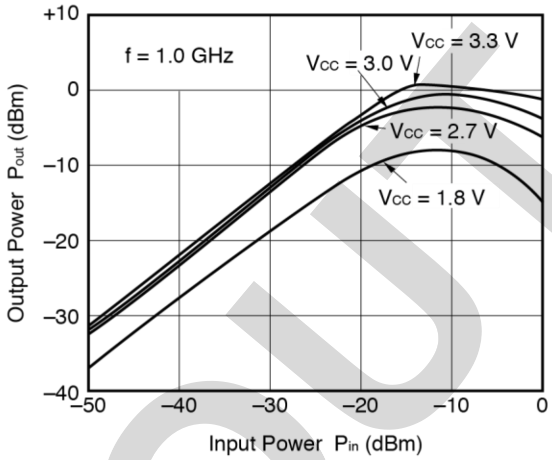
Remark The graphs indicate nominal characteristics.

— μPC2746TB —

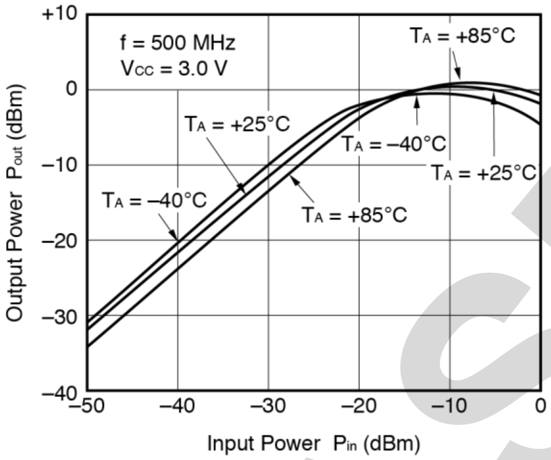
OUTPUT POWER vs. INPUT POWER



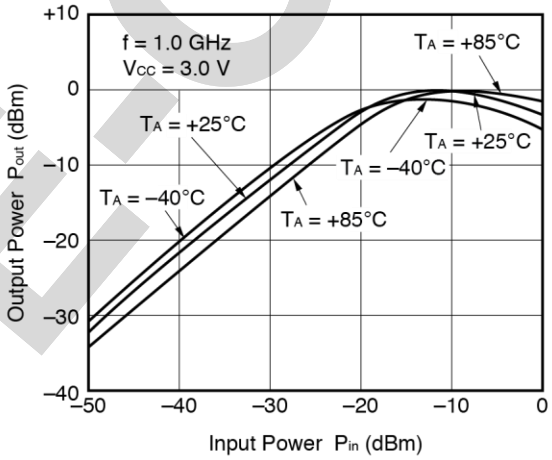
OUTPUT POWER vs. INPUT POWER



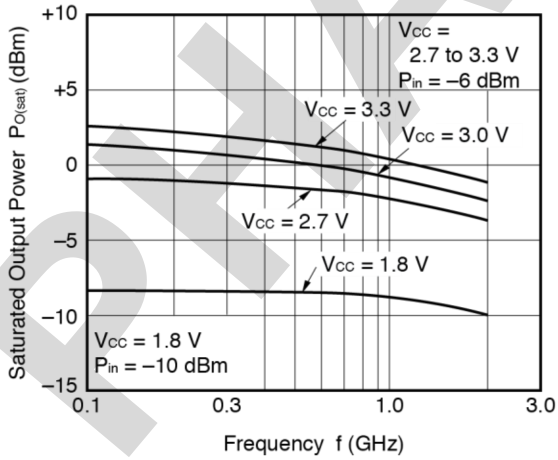
OUTPUT POWER vs. INPUT POWER



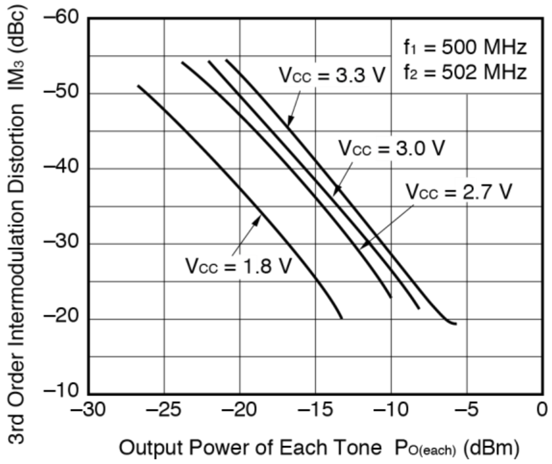
OUTPUT POWER vs. INPUT POWER



SATURATED OUTPUT POWER vs. FREQUENCY



3RD ORDER INTERMODULATION DISTORTION vs. OUTPUT POWER OF EACH TONE

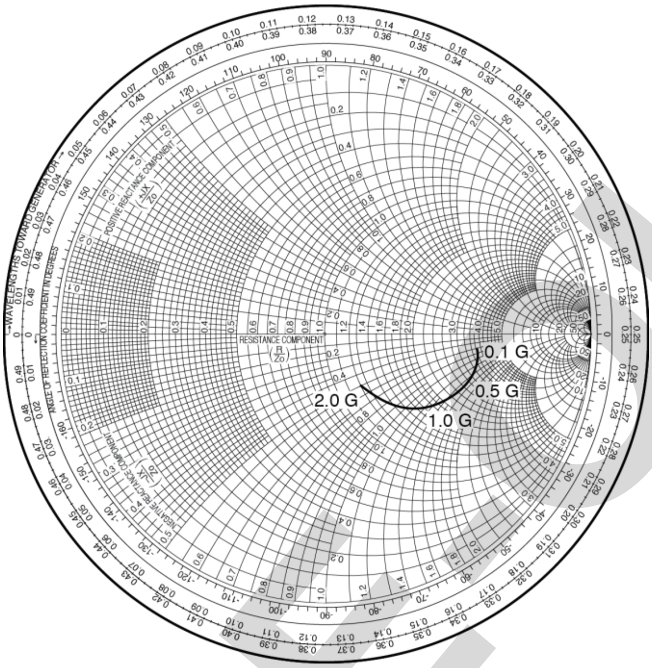


Remark The graphs indicate nominal characteristics.

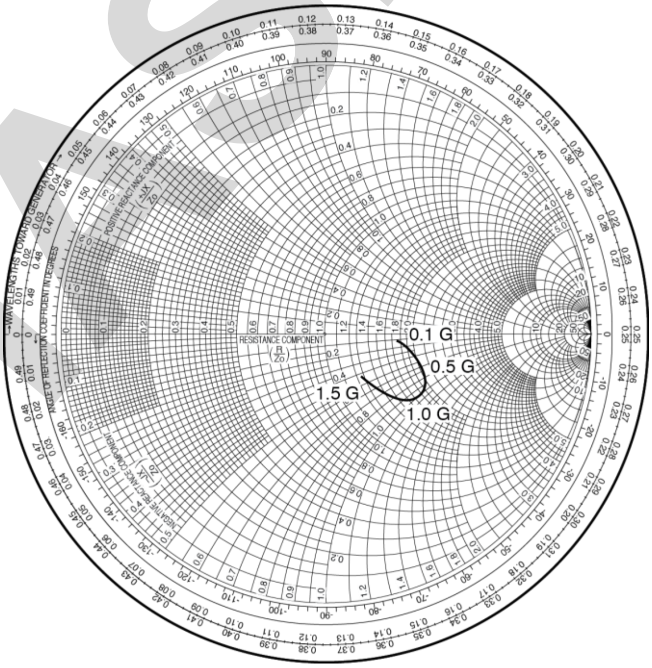
SMITH CHART (TA = +25°C, VCC = 3.0 V)

— μPC2746TB —

S11-FREQUENCY



S22-FREQUENCY



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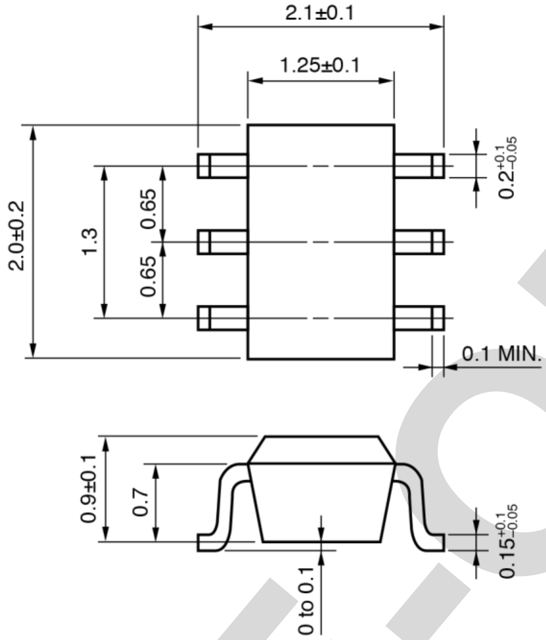
- [RF and Microwave] ® [Device Parameters]
- URL http://www.necel.com/microwave/en/

PACKAGE DIMENSIONS

6-PIN SUPER MINIMOLD (UNIT: mm)



NOTES ON CORRECT USE

(1) Observe precautions for handling because of electro-static sensitive devices.
(2) Form a ground pattern as widely as possible to minimize ground impedance (to prevent undesired oscillation). All the ground pins must be connected together with wide ground pattern to decrease impedance difference.
(3) The bypass capacitor should be attached to the V_{CC} pin.
(4) The DC cut capacitor must be attached to input pin and output pin.

RECOMMENDED SOLDERING CONDITIONS

This product should be soldered and mounted under the following recommended conditions. For soldering methods and conditions other than those recommended below, contact your nearby sales office.

Soldering Method	Soldering Conditions		Condition Symbol
Infrared Reflow	Peak temperature (package surface temperature) Time at peak temperature Time at temperature of 220°C or higher Preheating time at 120 to 180°C Maximum number of reflow processes Maximum chlorine content of rosin flux (% mass)	: 260°C or below : 10 seconds or less : 60 seconds or less : 120±30 seconds : 3 times : 0.2%(Wt.) or below	IR260
VPS	Peak temperature (package surface temperature) Time at temperature of 200°C or higher Preheating time at 120 to 150°C Maximum number of reflow processes Maximum chlorine content of rosin flux (% mass)	: 215°C or below : 25 to 40 seconds : 30 to 60 seconds : 3 times : 0.2%(Wt.) or below	VP215
Wave Soldering	Peak temperature (molten solder temperature) Time at peak temperature Preheating temperature (package surface temperature) Maximum number of flow processes Maximum chlorine content of rosin flux (% mass)	: 260°C or below : 10 seconds or less : 120°C or below : 1 time : 0.2%(Wt.) or below	WS260
Partial Heating	Peak temperature (pin temperature) Soldering time (per side of device) Maximum chlorine content of rosin flux (% mass)	: 350°C or below : 3 seconds or less : 0.2%(Wt.) or below	HS350

Caution Do not use different soldering methods together (except for partial heating).

NOTICE

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